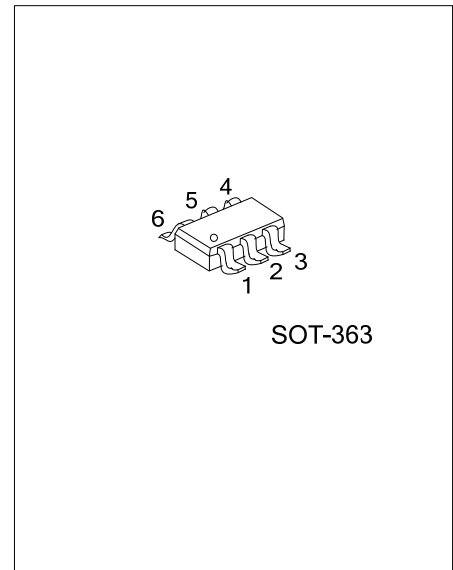




2N7002ZDW

Power MOSFET

300mA, 60V DUAL N-CANNEL ENHANCEMENT MODE POWER MOSFET



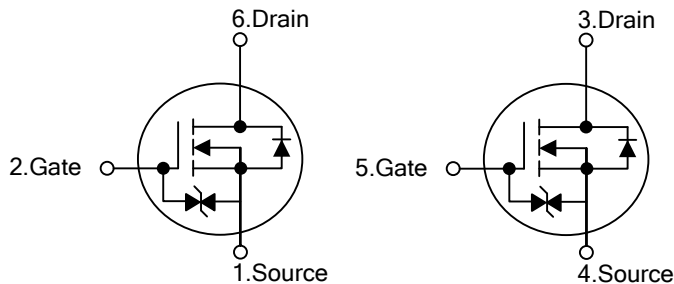
■ DESCRIPTION

The UTC **2N7002ZDW** uses advanced technology to provide excellent $R_{DS(ON)}$, low gate charge and low gate voltages during operation. This device is suitable for use as a load switch or in PWM applications.

■ FEATURES

- * Low Reverse Transfer Capacitance (C_{RSS} = typical 3.0 pF)
- * ESD Protected
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, High Ruggedness

■ SYMBOL

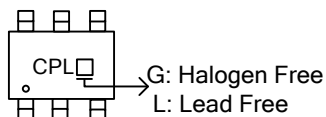


■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment						Packing
Lead Free	Halogen Free		1	2	3	4	5	6	
2N7002ZDWL-AL6-R	2N7002ZDWG-AL6-R	SOT-363	S1	G1	D2	S2	G2	D1	Tape Reel

<p>2N7002ZDWG-AL6-R</p> <ul style="list-style-type: none"> (1)Packing Type (2)Package Type (3)Halogen Free 	<ul style="list-style-type: none"> (1) R: Tape Reel (2) AL6: SOT-363 (3) G: Halogen Free, L: Lead Free
---	---

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise specified.)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	I_D	Continuous	300
		Pulse(Note 2)	800
Power Dissipation	P_D	200	mW
Derating above $T_A=25^\circ\text{C}$		1.6	mW/ $^\circ\text{C}$
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

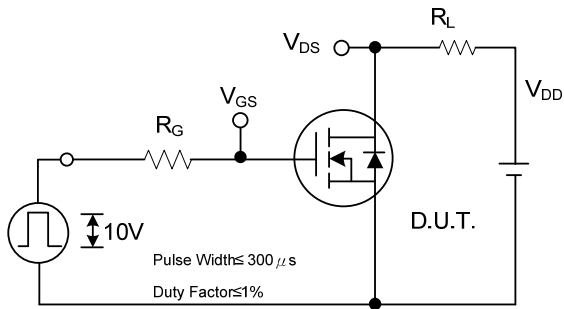
■ ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$, unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=10\mu A$	60			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$			1.0	μA
Gate-Source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 10	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=10V, I_D=1mA$	1.0	1.85	2.5	V
Static Drain-Source On-Resistance (Note)	$R_{DS(ON)}$	$V_{GS}=10V, I_D=0.3A, T_J=125^\circ\text{C}$			13.5	Ω
		$V_{GS}=5V, I_D=0.05A$			7.5	
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{DS}=25V, V_{GS}=0V, f=1.0MHz$		25	50	pF
Output Capacitance	C_{OSS}		10	25	pF	
Reverse Transfer Capacitance	C_{RSS}		3.0	5.0	pF	
SWITCHING PARAMETERS						
Turn-ON Delay Time	$t_{D(ON)}$	$I_D=0.2A, V_{DD}=30V, V_{GS}=10V,$		12	20	ns
Turn-OFF Delay Time	$t_{D(OFF)}$	$R_L=150\Omega, R_G=10\Omega$		20	30	
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=300mA$ (Note)		0.88	1.5	V
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				0.8	A
Maximum Continuous Drain-Source Diode Forward Current	I_S				300	mA

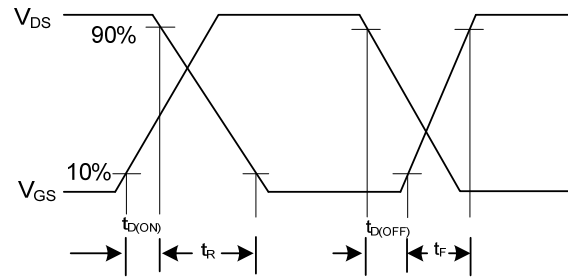
Note: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch. Minimum land pad size.

2. Pulse width $\leq 300\mu s$, Duty cycle $\leq 1\%$

■ TEST CIRCUITS AND WAVEFORMS



Switching Test Circuit



Switching Waveforms

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.